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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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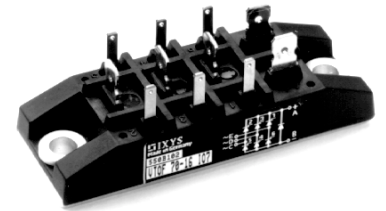
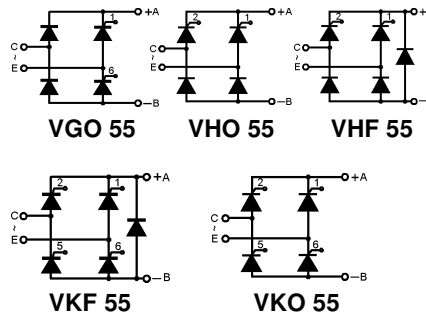


# Single Phase Rectifier Bridge

**$I_{dAV} = 53 \text{ A}$**   
 **$V_{RRM} = 800-1600 \text{ V}$**

Preliminary data

$V_{RSM}$ $V_{DSM}$ V	$V_{RRM}$ $V_{DRM}$ V	Type
800	800	xxx 55-08io7
1200	1200	xxx 55-12io7
1400	1400	xxx 55-14io7
1600	1600	xxx 55-16io7
xxx = type		



Symbol	Test Conditions	Maximum Ratings
$I_{dAV}$ ①	$T_K = 85^\circ\text{C}$ , module	53 A
$I_{dAVM}$ ①	module	53 A
$I_{FRMS}$ , $I_{TRMS}$	per leg	41 A
$I_{FSM}$ , $I_{TSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $V_R = 0 \text{ V}$	$t = 10 \text{ ms}$ (50 Hz), sine 550 A $t = 8.3 \text{ ms}$ (60 Hz), sine 600 A
	$T_{VJ} = T_{VJM}$ $V_R = 0 \text{ V}$	$t = 10 \text{ ms}$ (50 Hz), sine 500 A $t = 8.3 \text{ ms}$ (60 Hz), sine 550 A
$I^2t$	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0 \text{ V}$	$t = 10 \text{ ms}$ (50 Hz), sine 1520 A <sup>2</sup> s $t = 8.3 \text{ ms}$ (60 Hz), sine 1520 A <sup>2</sup> s
	$T_{VJ} = T_{VJM}$ $V_R = 0 \text{ V}$	$t = 10 \text{ ms}$ (50 Hz), sine 1250 A <sup>2</sup> s $t = 8.3 \text{ ms}$ (60 Hz), sine 1250 A <sup>2</sup> s
$(di/dt)_{cr}$	$T_{VJ} = 125^\circ\text{C}$ $f = 50 \text{ Hz}$ , $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.3 \text{ A}$ , $di_G/dt = 0.3 \text{ A}/\mu\text{s}$	repetitive, $I_T = 50 \text{ A}$ 150 A/ $\mu\text{s}$
		non repetitive, $I_T = 1/2 \cdot I_{dAV}$ 500 A/ $\mu\text{s}$
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$ ; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$ ; method 1 (linear voltage rise)	1000 V/ $\mu\text{s}$
$V_{RGM}$		10 V
$P_{GM}$	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$	$t_p = 30 \mu\text{s}$ $\leq 10 \text{ W}$
		$t_p = 500 \mu\text{s}$ $\leq 5 \text{ W}$
		$t_p = 10 \text{ ms}$ $\leq 1 \text{ W}$
$P_{GAVM}$		0.5 W
$T_{VJ}$		-40...+125 °C
$T_{VJM}$		125 °C
$T_{stg}$		-40...+125 °C
$V_{ISOL}$	50/60 Hz, RMS	$t = 1 \text{ min}$ 2500 V~ $t = 1 \text{ s}$ 3000 V~
	$I_{ISOL} \leq 1 \text{ mA}$	
$M_d$	Mounting torque (M5) (10-32 UNF)	5 ± 15 % Nm
		44 ± 15 % lb.in.
Weight		110 g

## Features

- Package with copper base plate
- Isolation voltage 3000 V~
- Planar passivated chips
- Low forward voltage drop
- 1/4" fast-on power terminals

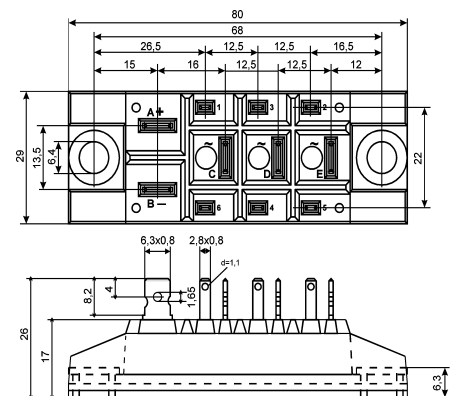
## Applications

- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

## Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- Small and light weight

## Dimensions in mm (1 mm = 0.0394")



Data according to IEC 60747 refer to a single diode/thyristor unless otherwise stated  
 ① for resistive load at bridge output. IXYS reserves the right to change limits, test conditions and dimensions.

Symbol	Test Conditions	Characteristic Values	
$I_D, I_R$	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	$\leq$	5 mA
$V_T$	$I_T = 80 \text{ A}; T_{VJ} = 25^\circ\text{C}$	$\leq$	1.64 V
$V_{T0}$	For power-loss calculations only		0.85 V
$r_T$			11 m $\Omega$
$V_{GT}$	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	$\leq$	1.5 V
	$T_{VJ} = -40^\circ\text{C}$	$\leq$	1.6 V
$I_{GT}$	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	$\leq$	100 mA
	$T_{VJ} = -40^\circ\text{C}$	$\leq$	200 mA
$V_{GD}$	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	$\leq$	0.2 V
$I_{GD}$		$\leq$	5 mA
$I_L$	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	$\leq$	450 mA
$I_H$	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	$\leq$	200 mA
$t_{gd}$	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	$\leq$	2 $\mu\text{s}$
$t_q$	$T_{VJ} = T_{VJM}; I_T = 20 \text{ A}, t_p = 200 \mu\text{s}; di/dt = -10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 15 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	typ.	250 $\mu\text{s}$
$R_{thJC}$	per thyristor / Diode; DC		0.9 K/W
	per module		0.18 K/W
$R_{thJK}$	per thyristor / Diode; DC		1.1 K/W
	per module		0.22 K/W
$d_s$	Creeping distance on surface		16.1 mm
$d_A$	Creepage distance in air		7.1 mm
$a$	Max. allowable acceleration		50 m/s <sup>2</sup>